Highly Responsive Phototransistors based on the 2,6-bis(4-methoxyphenyl)anthracene Single Crystal

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Supporting Information Figure S1. Transfer curves of the single crystal based phototransistor under different color LED illumination (central wavelength of Red, Green and Blue lights are 620 nm, 520 nm and 450 nm, respectively).
Supporting Information Figure S2. Phototransistors performance with different channel widths, (a) Id-Vg curves for the three types of phototransistors and (b) photo responsivity of the three types of phototransistors. (A represent L = 98 μm, W = 980 μm; B represent L = 98 μm, W = 490 μm; C represent L = 98 μm, W = 294 μm.)
Supporting Information Figure S3. BOPAnt single crystal phototransistors device with channel length and channel width of 200 μm and 65 μm.